

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-4. (Cancelled).

5. (Currently Amended): A method of manufacturing a semiconductor integrated device, comprising:

a first step of ~~coating resin mixed with microparticles on at least one surface of~~ laminating a semiconductor substrate on which a semiconductor ~~integrated circuit is~~ plurality of semiconductor chips are formed, and ~~laminating a support substrate on the semiconductor substrate to hold the resin between the two substrates; and~~ with resin mixed with microparticles being interposed between the semiconductor substrate and the support substrate;

a second step of pushing the support substrate against the semiconductor substrate, ~~wherein;~~

~~no connection terminals are provided between the surface of the semiconductor substrate and the support substrate, and wherein~~

a third step of arranging wiring to achieve contact from the semiconductor chips; and

a fourth step of dividing the semiconductor chips along scrub lines to form the semiconductor integrated device, and wherein

in the second step, the support substrate is pushed against the semiconductor substrate while keeping a distance between the semiconductor substrate and the support substrate larger than the maximum particle diameter of the microparticles.

6. (Original): The method of manufacturing a semiconductor device of claim 5, further comprising a step of hardening the resin by subjecting it to a heat treatment process after the second step, and wherein in the second step the distance between the semiconductor substrate and the support substrate is kept larger than the sum of a contraction amount by which the film thickness of the resin contracts during the hardening step and the maximum particle diameter of the microparticles.

7. (Original): The method of manufacturing a semiconductor device of claim 5, further comprising, before the first step, a step of etching the semiconductor substrate to reduce the thickness of the semiconductor substrate.

8. (Original): A method of manufacturing a semiconductor integrated device, comprising:

a first step of coating a first resin layer mixed with microparticles on at least one surface of a semiconductor substrate on which a semiconductor integrated circuit is formed;

a second step of hardening the first resin layer coated in the first step;
and

a third step of coating a second resin layer not containing microparticles on the first resin layer hardened in the second step, wherein

in the second step, hardening is carried out so that the film thickness of the first resin layer after hardening is kept larger than the maximum particle diameter of the microparticles.

9. (Original): The method of manufacturing a semiconductor device of claim 8, further comprising, before the first step, a step of etching a rear surface of the semiconductor substrate to make the semiconductor substrate thin.